



Features

- For surface mount applications
- High forward surge current capability
- Low profile package
- Low power loss, high efficiency
- Metal silicon junction,majority carriers conduction

GA5



Marking Code :

SS12-PJ: SS12
SS14-PJ: SS14
SS16-PJ: SS16
SS18-PJ: SS18
SS110-PJ: SS110
SS112-PJ: SS112
SS115-PJ: SS115
SS120-PJ: SS120

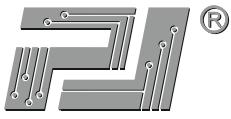
Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

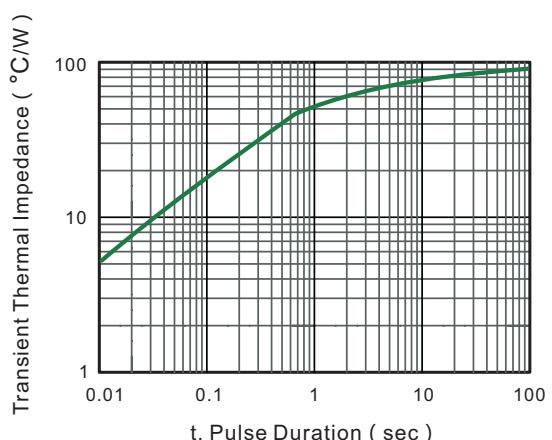
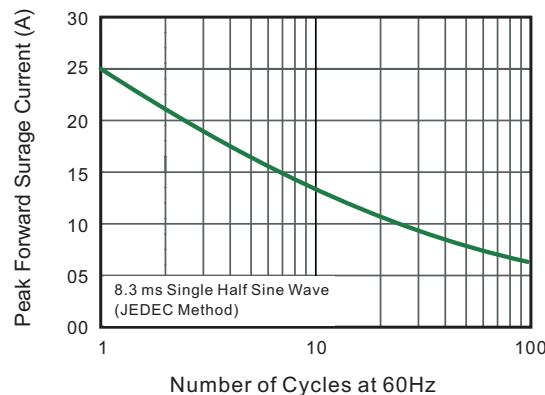
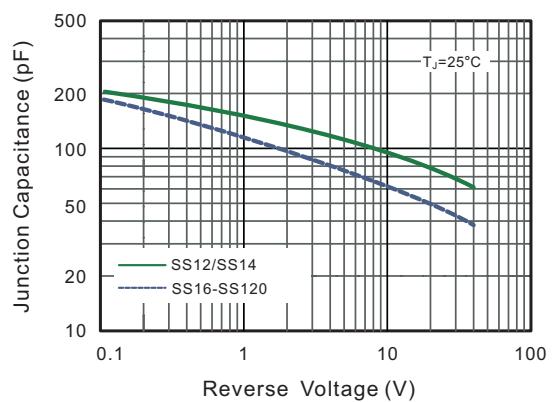
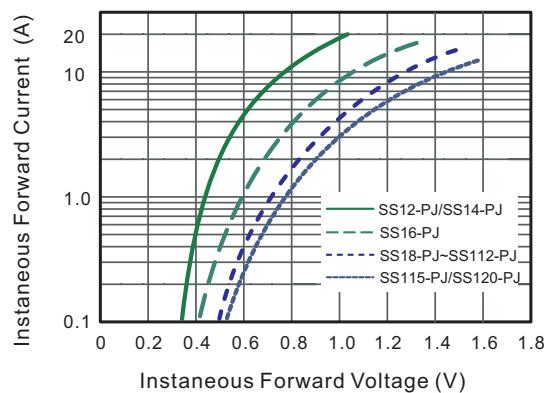
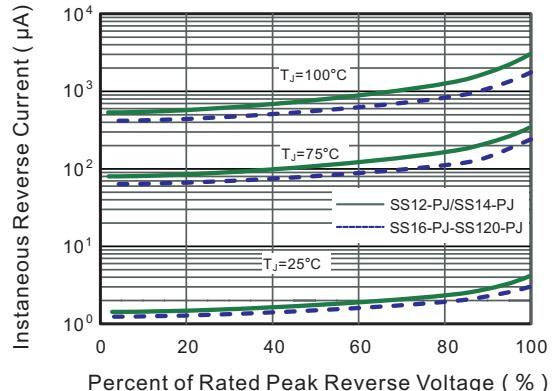
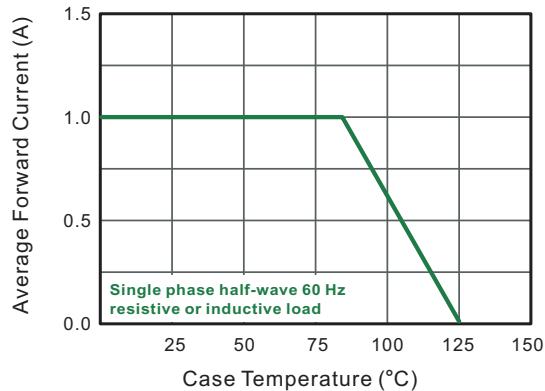
Parameter	Symbol	SS12 -PJ	SS14 -PJ	SS16 -PJ	SS18 -PJ	SS110 -PJ	SS112 -PJ	SS115 -PJ	SS120 -PJ	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS Voltage	V _{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	I _(AV)					1.0				A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}					25				A
Maximum Instantaneous Forward Voltage at 1 A	V _F		0.55	0.70		0.85		0.90		V
Maximum DC Reverse Current at Rated DC Blocking Voltage T _A = 25 °C T _A = 100 °C	I _R		0.3			0.2		0.1		mA
			10			5		2		
Typical Junction Capacitance ^{Note1}	C _j	110				80				pF
Typical Thermal Resistance ^{Note2}	R _{θJA}				90					°C/W
Operating Junction Temperature Range	T _J				-55 to +125					°C
Storage Temperature Range	T _{STG}				-55 to +150					°C

Note:

1. Measured at 1 MHz and applied reverse voltage of 4 V DC.
2. P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.



Typical Characteristic Curves

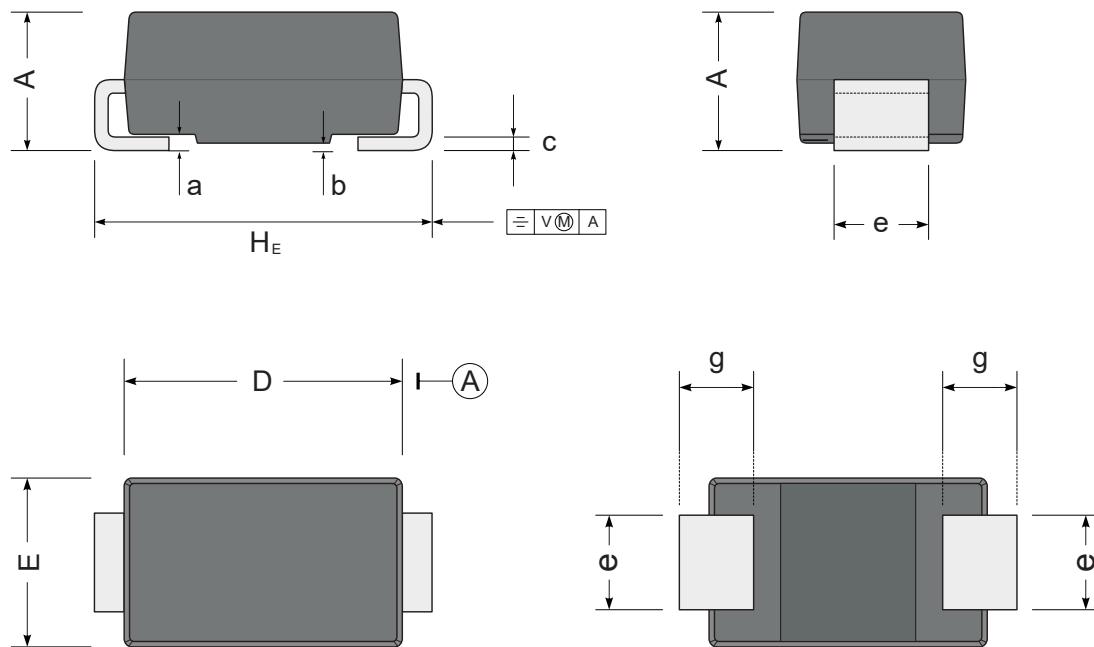




Package Outline

SMA

Dimensions in mm



UNIT		A	D	E	H _E	c	e	g	b	a
mm	max	2.2	4.5	2.7	5.2	0.31	1.6	1.5	0.2	0.3
	min	1.9	4.0	2.3	4.7	0.15	1.3	0.9	0.05	
mil	max	87	181	106	205	12	63	59	7.9	12
	min	75	157	91	185	6	51	35	2	